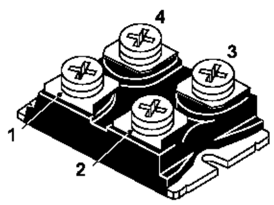
SGS-THOMSON MICROELECTRONICS

BUF460AV

NPN TRANSISTOR POWER MODULE

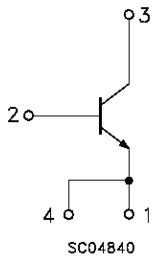
- EASY TO DRIVE TECHNOLOGY (ETD)
- HIGH CURRENT POWER BIPOLAR MODULE
- VERY LOW R_{th} JUNCTION CASE
- SPECIFIED ACCIDENTAL OVERLOAD AREAS
- ISOLATED CASE (2500V RMS)
- EASY TO MOUNT
- LOW INTERNAL PARASITIC INDUCTANCE

APPLICATIONS:
- MOTOR CONTROL
- SMPS & UPS
- WELDING EQUIPMENT



ISOTOP

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CEV}	Collector-Emitter Voltage (V_{BE} = -5 V)	1000	V
$V_{CEO(sus)}$	Collector-Emitter Voltage (I_B = 0)	450	V
V_{EBO}	Emitter-Base Voltage (I_C = 0)	7	V
I_C	Collector Current	80	A
I_{CM}	Collector Peak Current (t_p = 10 ms)	160	A
I_B	Base Current	18	A
I_{BM}	Base Peak Current (t_p = 10 ms)	27	A
P_{tot}	Total Dissipation at T_c = 25 ^oC	270	W
T_{stg}	Storage Temperature	-65 to 150	^oC
T_j	Max Operation Junction Temperature	150	^oC
V_{ISO}	Insulation Withstand Voltage (AC-RMS)	2500	V

THERMAL DATA

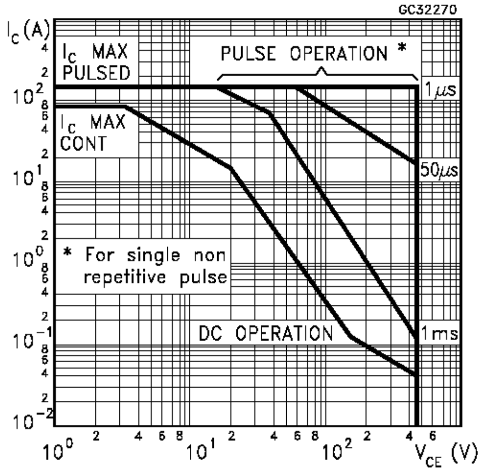
$R_{thj-case}$ R_{thc-h}	Thermal Resistance Junction-case Thermal Resistance Case-heatsink With Conductive Grease Applied	Max Max	0.41 0.05	$^oC/W$ $^oC/W$

ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

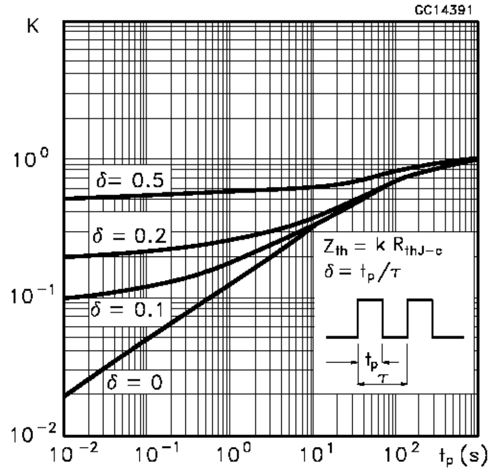
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CER}	Collector Cut-off Current (R_{BE} = 5 Ω)	$V_{CE} = V_{CEV}$ $V_{CE} = V_{CEV}$ T_j = 100 ^oC			0.2 2	mA mA
I_{CEV}	Collector Cut-off Current (V_{BE} = -1.5V)	$V_{CE} = V_{CEV}$ $V_{CE} = V_{CEV}$ T_j = 100 ^oC			0.2 2	mA mA
I_{EBO}	Emitter Cut-off Current (I_C = 0)	V_{EB} = 5 V			1	mA
$V_{CEO(SUS)}$*	Collector-Emitter Sustaining Voltage	I_C = 0.2 A L = 25 mH V_{clamp} = 450 V	450			V
h_{FE}*	DC Current Gain	I_C = 60 A V_{CE} = 5 V		15		
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 30 A I_B = 3 A I_C = 30 A I_B = 3 A T_j = 100 ^oC I_C = 60 A I_B = 12 A I_C = 60 A I_B = 12 A T_j = 100 ^oC		0.35 0.5 	 2 2	V V V V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C = 60 A I_B = 12 A I_C = 60 A I_B = 12 A T_j = 100 ^oC		1.1 	 1.5	V V
di_C/dt	Rate of Rise of On-state Collector	V_{CC} = 300 V R_C = 0 t_p = 3 μs I_{B1} = 18 A T_j = 100 ^oC	150			A/μs
V_{CE}(3 μs)•	Collector-Emitter Dynamic Voltage	V_{CC} = 300 V R_C = 30 Ω I_{B1} = 18 A T_j = 100 ^oC		4	6	V
V_{CE}(5 μs)•	Collector-Emitter Dynamic Voltage	V_{CC} = 300 V R_C = 30 Ω I_{B1} = 18 A T_j = 100 ^oC		2	3	V
t_s t_f t_c	Storage Time Fall Time Cross-over Time	I_C = 30 A V_{CC} = 50 V V_{BB} = -5 V R_{BB} = 0.2 Ω V_{clamp} = 400 V I_{B1} = 3 A L = 25 μH T_j = 100 ^oC		4.5 0.1 0.3	5 0.2 5	μs μs μs
V_{CEW}	Maximum Collector Emitter Voltage Without Snubber	I_{CWoff} = 80 A I_{B1} = 16 A V_{BB} = -5 V V_{CC} = 50 V L = 80 μH R_{BB} = 0.2 Ω T_j = 125 ^oC	400			V

∗ Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

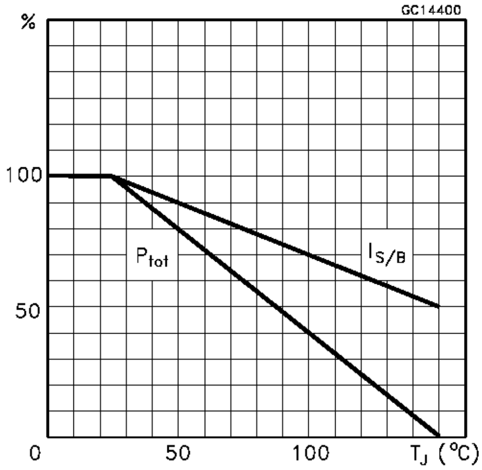
Safe Operating Areas



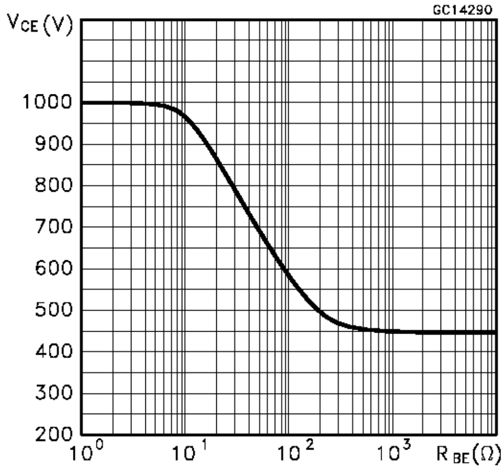
Thermal Impedance



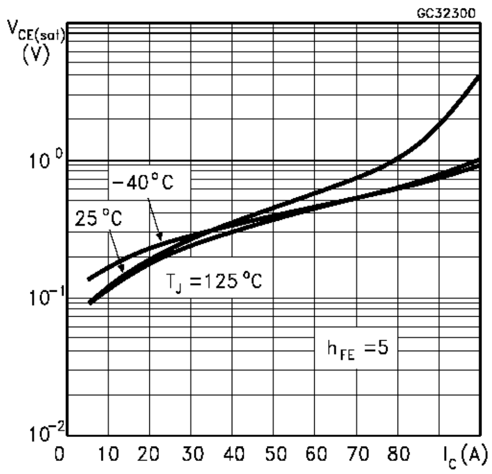
Derating Curve



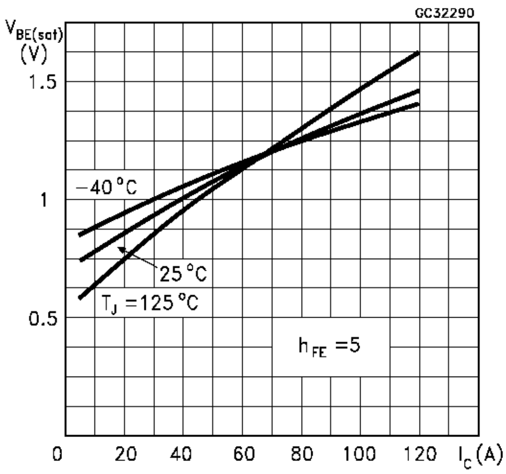
Collector-Emitter Voltage Versus Base-Emitter Resistance



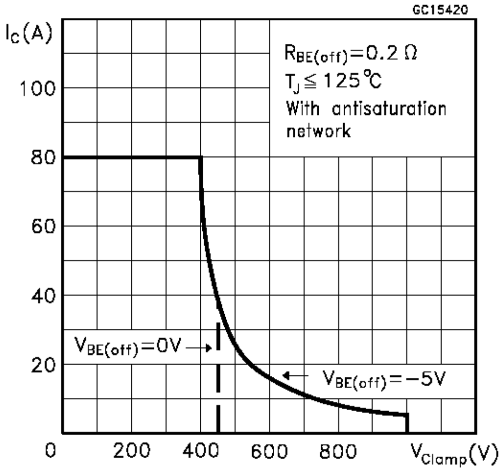
Collector-Emitter Saturation Voltage



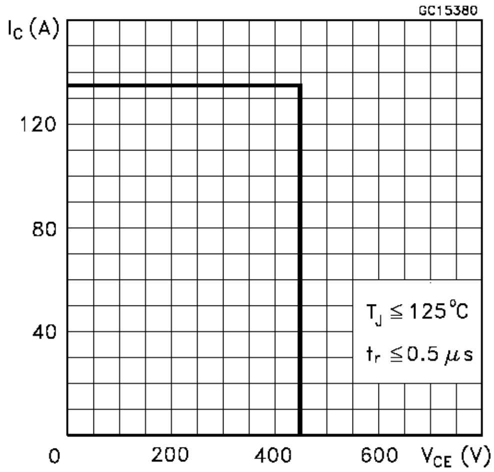
Base-Emitter Saturation Voltage



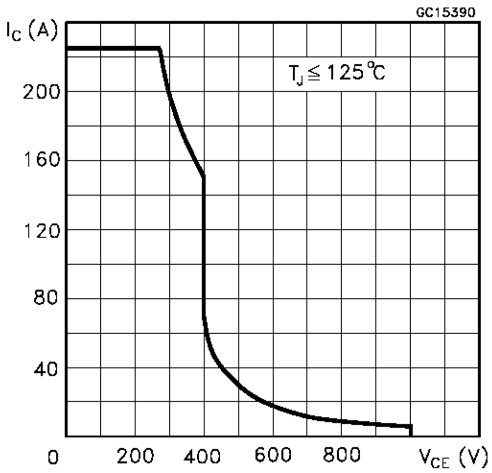
Reverse Biased SOA



Forward Biased SOA



Reverse Biased SOA



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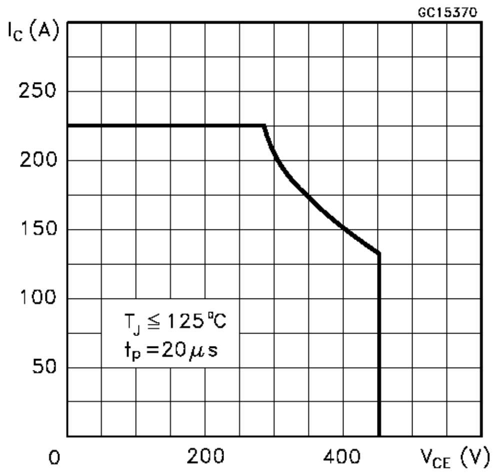
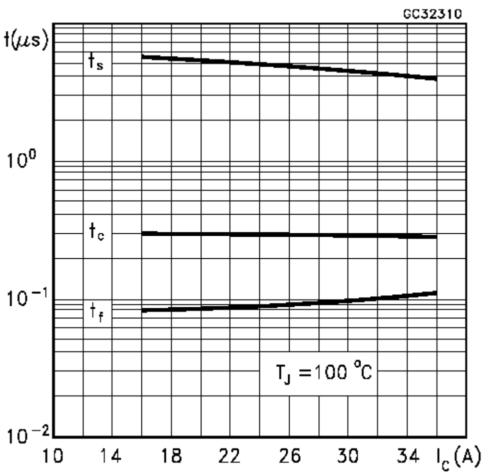
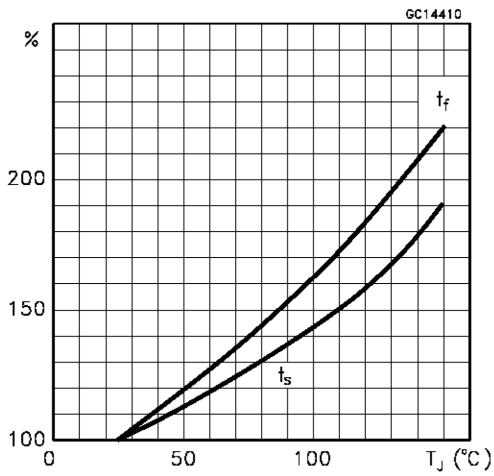


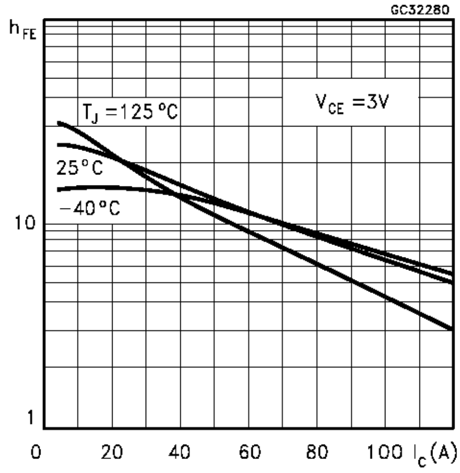
Switching Time Inductive Load



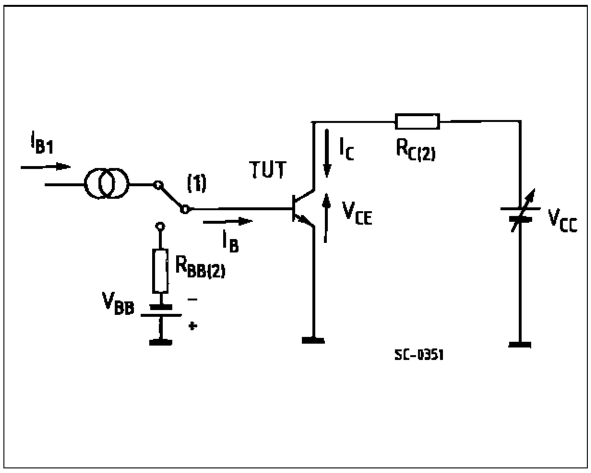
Switching Time Inductive Load Versus Temperature



DC Current Gain

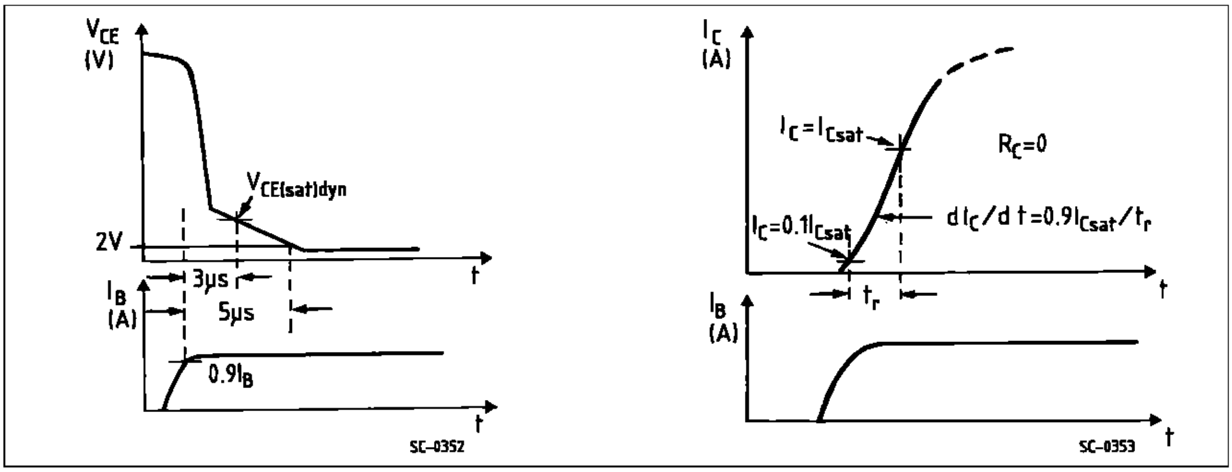


Turn-off Switching Test Circuit

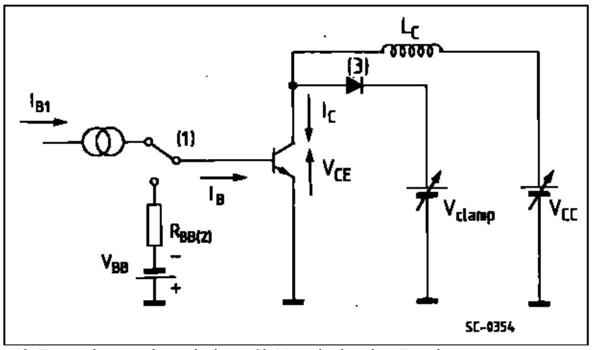


1) Fast electronic switch 2) Non-inductive Resistor

Turn-on Switching Waveforms.

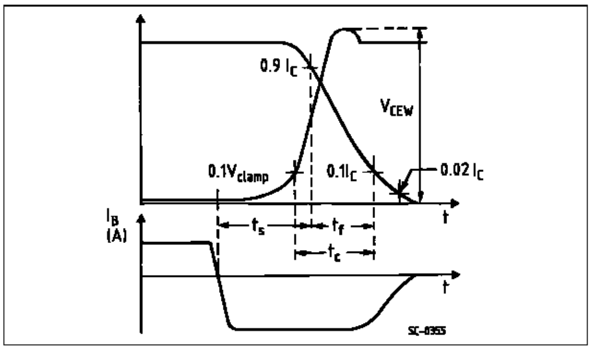


Turn-off Switching Test Circuit



1) Fast electronic switch 2) Non-inductive Resistor
3) Fast recovery rectifier

Turn-off Switching Waveforms.



ISOTOP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.466		0.480
B	8.9		9.1	0.350		0.358
C	1.95		2.05	0.076		0.080
D	0.75		0.85	0.029		0.033
E	12.6		12.8	0.496		0.503
F	25.15		25.5	0.990		1.003
G	31.5		31.7	1.240		1.248
H	4			0.157		
J	4.1		4.3	0.161		0.169
K	14.9		15.1	0.586		0.594
L	30.1		30.3	1.185		1.193
M	37.8		38.2	1.488		1.503
N	4			0.157		
O	7.8		8.2	0.307		0.322